
HD74HCT563/HD74HCT573

Octal Transparent Latches (with 3-state outputs)

HITACHI

Description

When the latch enable (LE) input is high, the Q outputs of HD74HCT563 will follow the inversion of the D inputs and the Q outputs of HD74HCT573 will follow the D inputs.

When the latch enable goes low, data at the D inputs will be retained at the outputs until latch enabled returns high again. When a high logic level is applied to the output control input, all outputs go to a high impedance state, regardless of what signals are present at the other inputs and the state of the storage elements.

Features

- LSTTL Output Logic Level Compatibility as well as CMOS Output Compatibility
- High Speed Operation: t_{pd} (D to Q, \bar{Q}) = 13 ns typ ($C_L = 50$ pF)
- High Output Current: Fanout of 15 LSTTL Loads
- Wide Operating Voltage: $V_{CC} = 4.5$ to 5.5 V
- Low Input Current: 1 μ A max
- Low Quiescent Supply Current: I_{CC} (static) = 4 μ A max ($T_a = 25^\circ\text{C}$)

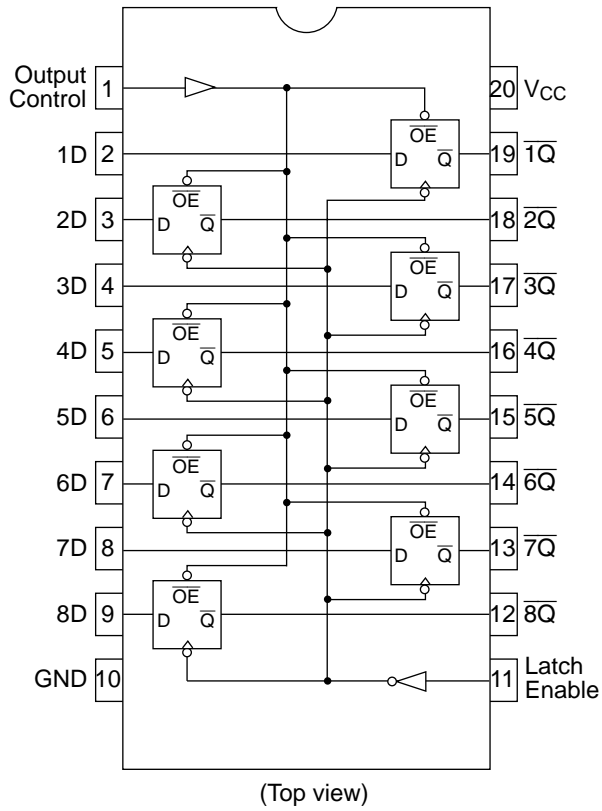
Function Table

Output Control	Latch Enable	Data	Outputs	
			HD74HCT563	HD74HCT573
L	H	H	L	H
L	H	L	H	L
L	L	X	\bar{Q}_0	Q_0
H	X	X	Z	Z

HD74HCT563/HD74HCT573

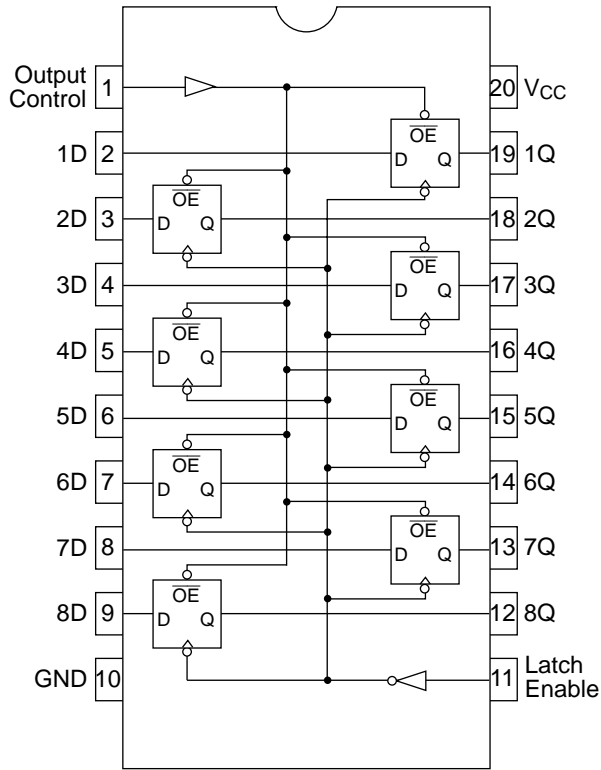
Pin Arrangement

HD74HCT563



HITACHI

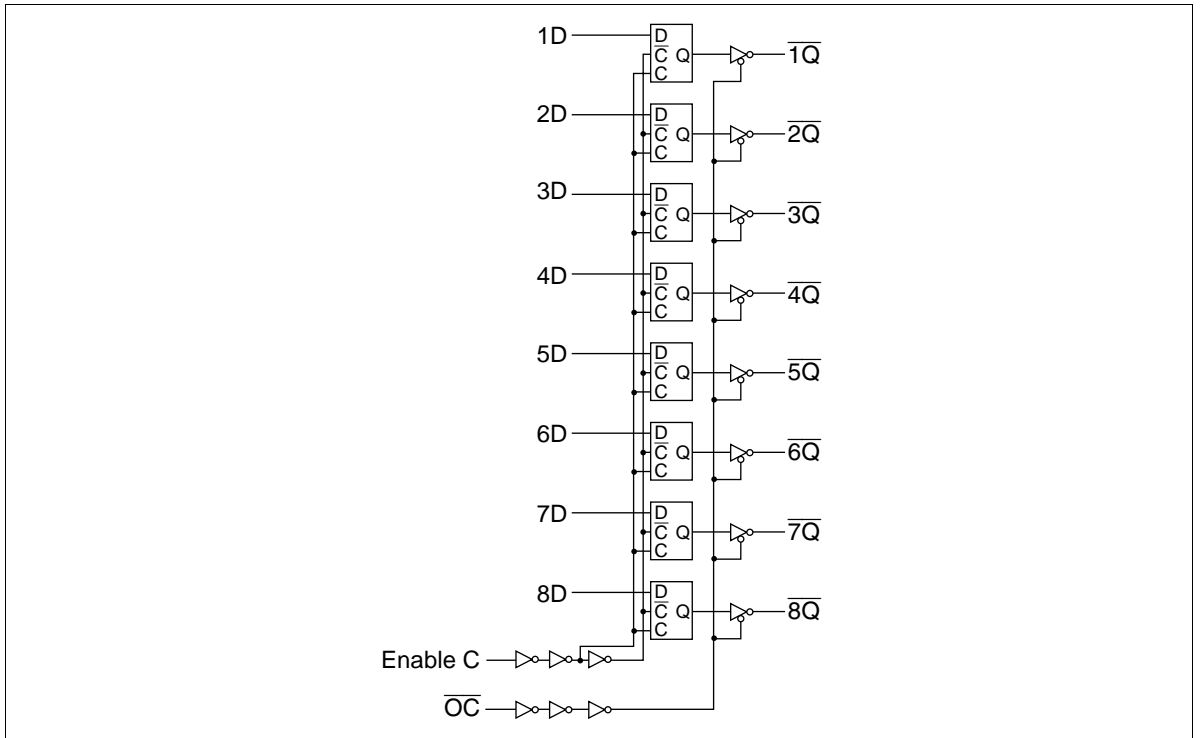
HD74HCT573



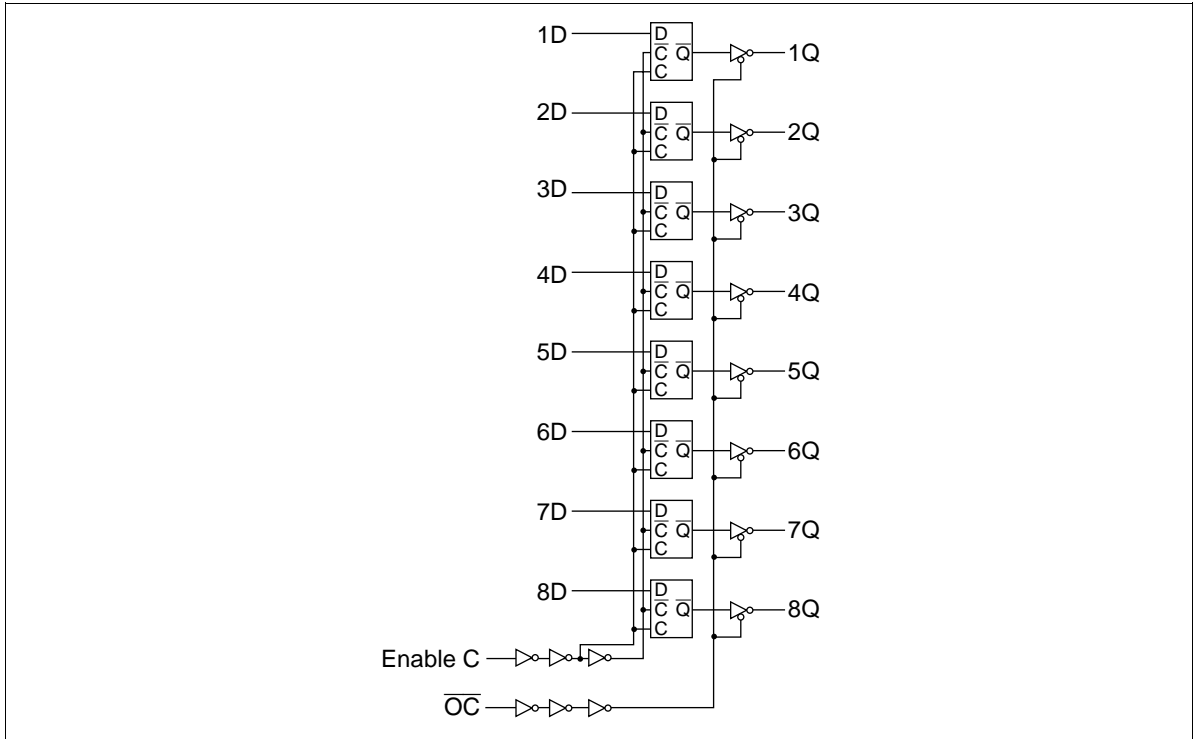
(Top view)

Block Diagram

HD74HCT563



HD74HCT573



Absolute Maximum Ratings

Item	Symbol	Rating	Unit
Supply voltage range	V_{CC}	-0.5 to +7.0	V
Input voltage	V_{IN}	-0.5 to $V_{CC} + 0.5$	V
Output voltage	V_{OUT}	-0.5 to $V_{CC} + 0.5$	V
DC current drain per pin	I_{OUT}	± 35	mA
DC current drain per V_{CC} , GND	I_{CC}, I_{GND}	± 75	mA
DC input diode current	I_{IK}	± 20	mA
DC output diode current	I_{OK}	± 20	mA
Power dissipation per package	P_T	500	mW
Storage temperature	T_{stg}	-65 to +150	$^{\circ}C$

HD74HCT563/HD74HCT573

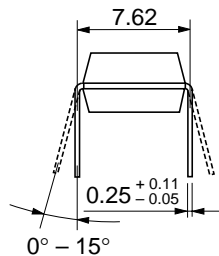
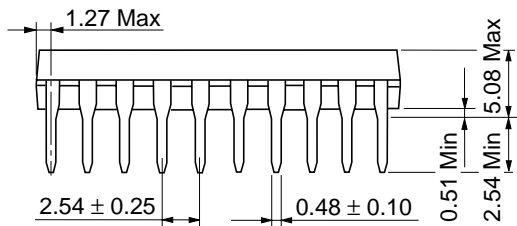
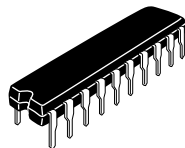
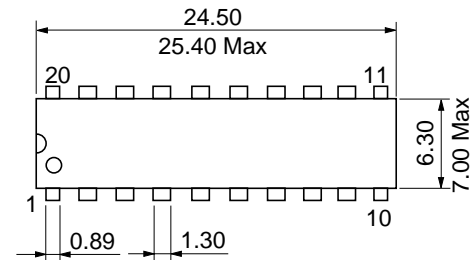
DC Characteristics

Item	Symbol	Ta = 25°C		Ta = -40 to +85°C		Unit	Test Conditions		
		Min	Typ	Max	Min		Max	V _{CC} (V)	
Input voltage	V _{IH}	2.0	—	—	2.0	—	V	4.5 to 5.5	
	V _{IL}	—	—	0.8	—	0.8	V	4.5 to 5.5	
Output voltage	V _{OH}	4.4	—	—	4.4	—	V	4.5	Vin = V _{IH} or V _{IL} I _{OH} = -20 μA
		4.18	—	—	4.13	—	V	4.5	
	V _{OL}	—	—	0.1	—	0.1	V	4.5	Vin = V _{IH} or V _{IL} I _{OL} = 20 μA
		—	—	0.26	—	0.33	V	4.5	
Off-state output current	I _{OZ}	—	—	±0.5	—	±5.0	μA	5.5	Vin = V _{IH} or V _{IL} , Vout = V _{CC} or GND
Input current	I _{in}	—	—	±0.1	—	±1.0	μA	5.5	Vin = V _{CC} or GND
Quiescent current	I _{CC}	—	—	4.0	—	40	μA	5.5	Vin = V _{CC} or GND, Iout = 0 μA

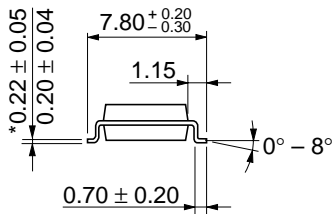
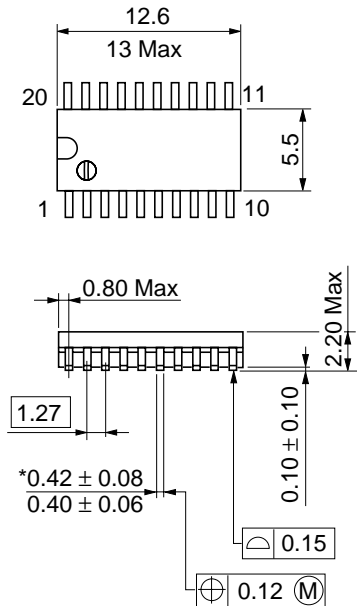
AC Characteristics (C_L = 50 pF, Input t_r = t_f = 6 ns)

Item	Symbol	Ta = 25°C		Ta = -40 to +85°C		Unit	Test Conditions		
		Min	Typ	Max	Min		Max	V _{CC} (V)	
Propagation delay time	t _{PLH}	—	13	22	—	28	ns	4.5	Data to Q, \bar{Q}
	t _{PHL}	—	13	22	—	28	ns	4.5	
	t _{PLH}	—	14	23	—	29	ns	4.5	Enable G to Q, \bar{Q}
	t _{PHL}	—	14	23	—	29	ns	4.5	
Output enable time	t _{ZL}	—	14	30	—	38	ns	4.5	
	t _{ZH}	—	15	30	—	38	ns	4.5	
Output disable time	t _{LZ}	—	16	30	—	38	ns	4.5	
	t _{HZ}	—	17	30	—	38	ns	4.5	
Setup time	t _{su}	12	3	—	15	—	ns	4.5	
Hold time	t _h	5	-1	—	5	—	ns	4.5	
Pulse width	t _w	16	4	—	20	—	ns	4.5	
Output rise/fall time	t _{TLH}	—	4	12	—	15	ns	4.5	
	t _{THL}	—	4	12	—	15	ns	4.5	
Input capacitance	C _{in}	—	5	10	—	10	pF	—	

HITACHI

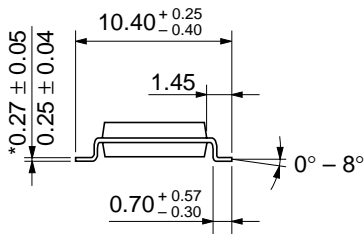
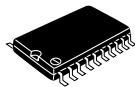
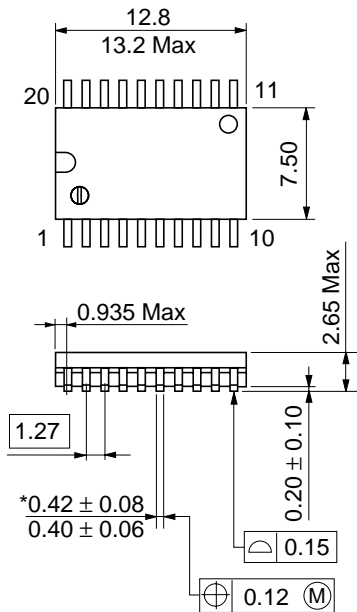


Hitachi Code	DP-20N
JEDEC	—
EIAJ	Conforms
Weight (reference value)	1.26 g



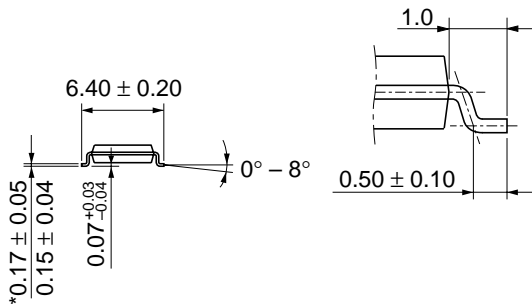
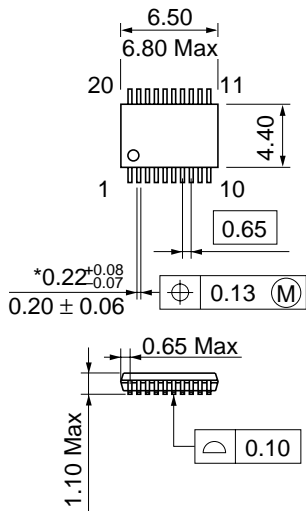
*Dimension including the plating thickness
Base material dimension

Hitachi Code	FP-20DA
JEDEC	—
EIAJ	Conforms
Weight (reference value)	0.31 g



Hitachi Code	FP-20DB
JEDEC	Conforms
EIAJ	—
Weight (reference value)	0.52 g

*Dimension including the plating thickness
 Base material dimension



Hitachi Code	TTP-20DA
JEDEC	—
EIAJ	—
Weight (reference value)	0.07 g

*Dimension including the plating thickness
Base material dimension

Cautions

1. Hitachi neither warrants nor grants licenses of any rights of Hitachi's or any third party's patent, copyright, trademark, or other intellectual property rights for information contained in this document. Hitachi bears no responsibility for problems that may arise with third party's rights, including intellectual property rights, in connection with use of the information contained in this document.
2. Products and product specifications may be subject to change without notice. Confirm that you have received the latest product standards or specifications before final design, purchase or use.
3. Hitachi makes every attempt to ensure that its products are of high quality and reliability. However, contact Hitachi's sales office before using the product in an application that demands especially high quality and reliability or where its failure or malfunction may directly threaten human life or cause risk of bodily injury, such as aerospace, aeronautics, nuclear power, combustion control, transportation, traffic, safety equipment or medical equipment for life support.
4. Design your application so that the product is used within the ranges guaranteed by Hitachi particularly for maximum rating, operating supply voltage range, heat radiation characteristics, installation conditions and other characteristics. Hitachi bears no responsibility for failure or damage when used beyond the guaranteed ranges. Even within the guaranteed ranges, consider normally foreseeable failure rates or failure modes in semiconductor devices and employ systemic measures such as fail-safes, so that the equipment incorporating Hitachi product does not cause bodily injury, fire or other consequential damage due to operation of the Hitachi product.
5. This product is not designed to be radiation resistant.
6. No one is permitted to reproduce or duplicate, in any form, the whole or part of this document without written approval from Hitachi.
7. Contact Hitachi's sales office for any questions regarding this document or Hitachi semiconductor products.

HITACHI

Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL North America : <http://semiconductor.hitachi.com/>
 Europe : <http://www.hitachi-eu.com/hel/ecg>
 Asia (Singapore) : <http://www.has.hitachi.com.sg/grp3/sicd/index.htm>
 Asia (Taiwan) : http://www.hitachi.com.tw/E/Product/SICD_Frame.htm
 Asia (HongKong) : <http://www.hitachi.com.hk/eng/bo/grp3/index.htm>
 Japan : <http://www.hitachi.co.jp/Sicd/indx.htm>

For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose, CA 95134
Tel: <1> (408) 433-1990
Fax: <1> (408) 433-0223

Hitachi Europe GmbH
Electronic components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia Ltd.
Taipei Branch Office
3F, Hung Kuo Building, No.167,
Tun-Hwa North Road, Taipei (105)
Tel: <886> (2) 2718-3666
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX

Copyright ' Hitachi, Ltd., 1999. All rights reserved. Printed in Japan.

HITACHI